

REMARKS

The Official Action mailed October 8, 2002 has been received and its contents carefully noted. Filed concurrently herewith is a *Continued Prosecution Application* and *Preliminary Amendment*. Applicant notes with appreciation the consideration of the Information Disclosure Statements filed on January 13, 2000, April 27, 2000, June 9, 2000, January 31, 2001, July 5, 2001, August 15, 2001, October 15, 2001, January 9, 2002, June 7, 2002 and July 9, 2002. However, Applicant has no record of receiving acknowledgement of the Information Disclosure Statement filed on January 3, 2001. The Official Action asserts that this IDS has not been received by the office. Therefore, a further copy of this IDS is attached together with a stamped receipt card from the Patent Office evidencing receipt on January 5, 2001. Copies of the references are believed to be of record, but should additional copies be needed for consideration, it is requested that the undersigned be notified so that such copies can be provided. Consideration of the references and return of an initialed PTO Form 1449 is respectfully requested at this time.

In accordance with MPEP § 819, it is respectfully noted that applicant has directed the claims in this CPA to a previously non-elected invention. Therefore, it is respectfully requested that applicant's earlier election not be carried forward in this CPA and that claims 13-17 and 46-81 as submitted herewith be examined on the merits in this application. It is respectfully submitted that claims 13-17 as amended herewith and new claims 46-81 are patentable over the prior art of record.

Should the Examiner believe that anything further would be desirable to place this application in better condition for allowance, the Examiner is invited to contact Applicant's undersigned attorney at the telephone number listed below.

Respectfully submitted,


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VERSION WITH MARKINGS TO SHOW CHANGES MADE

13. (Amended) A semiconductor device having an active matrix display device,
said display device comprising:

at least one first thin film transistor formed over a substrate;
a pixel electrode electrically connected to said first thin film
transistor;
a driver circuit including at least one second thin film transistor
formed over said substrate for driving said at least one first thin film transistor, said first
thin film transistor comprising:

a semiconductor island on an insulating surface over the substrate;
source and drain regions formed in the semiconductor island;
a channel region in the semiconductor island between the source and
drain regions;

a pair of [LDD] lightly doped regions formed between the channel region
and the source and drain regions wherein an impurity concentration in the lightly doped
regions is smaller than that in the source and drain regions;

a gate electrode formed over the semiconductor island with a gate
insulating film interposed therebetween wherein said gate electrode comprises at least
a first conductive layer and a second conductive layer formed on the first conductive
layer, said first conductive layer having a pair of tapered portions, which extend beyond
side edges of the second conductive layer,

wherein the pair of [the LDD] lightly doped regions has a pair of first
portions which are overlapped by the pair of [the] tapered portions of the first conductive
layer, and a pair of second portions which extend beyond side edges of the first
conductive layer.

16. (Amended) A device according to claim 13, wherein the first conductive layer
includes at least one selected from the group consisting of chromium (Cr), tantalum
(Ta), an n-type silicon containing phosphorus, titanium (Ti), tungsten (W), and
molybdenum (Mo) while the second conductive layer includes at least one selected from

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the group consisting of aluminum (Al), copper (Cu), chromium (Cr), tantalum (Ta), titanium (Ti), tungsten (W), molybdenum (Mo), an n-type silicon containing phosphorus, and silicide.